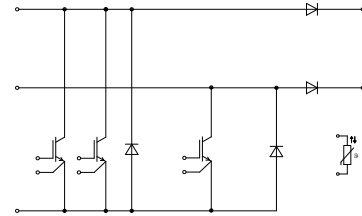
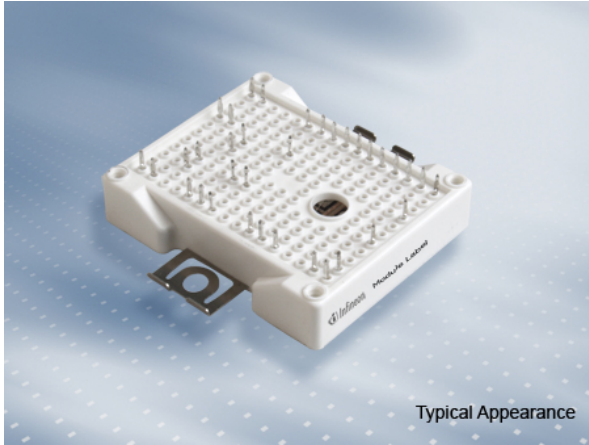


初步数据 / Preliminary Data



$V_{CES} = 1200V$   
 $I_{C\ nom} = 40A / I_{CRM} = 80A$

典型应用

- 太阳能应用

Typical Applications

- Solar Applications

电气特性

- 高速IGBT H3
- 低开关损耗

Electrical Features

- High Speed IGBT H3
- Low Switching Losses

机械特性

- 低热阻的三氧化二铝 (  $Al_2O_3$  衬底
- 集成NTC温度传感器
- 紧凑型设计
- PressFIT 压接技术

Mechanical Features

- $Al_2O_3$  Substrate with Low Thermal Resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT Contact Technology

Module Label Code

Barcode Code 128



Content of the Code

Digit

Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

DMX - Code



prepared by: CM	date of publication: 2013-11-25	
approved by: MB	revision: 2.0	UL approved (E83335)

初步数据  
Preliminary Data

反极性保护二极管A / Inverse-polarity protection diode A  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_c = 80^{\circ}\text{C}$	$I_{FRMSM}$	50	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_c = 80^{\circ}\text{C}$	$I_{RMSM}$	60	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I_{FSM}$	360 290	A A
I <sup>2</sup> t-值 I <sup>2</sup> t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I <sup>2</sup> t	650 420	A <sup>2</sup> s A <sup>2</sup> s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 30\text{ A}$	$V_F$		0,95		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$	$I_R$		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	$R_{thJC}$		0,80	0,90	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		0,80		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$				$^{\circ}\text{C}$

反极性保护二极管B / Inverse-polarity protection diode B  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_c = 80^{\circ}\text{C}$	$I_{FRMSM}$	30	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_c = 80^{\circ}\text{C}$	$I_{RMSM}$	60	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I_{FSM}$	290 245	A A
I <sup>2</sup> t-值 I <sup>2</sup> t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I <sup>2</sup> t	420 300	A <sup>2</sup> s A <sup>2</sup> s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 20\text{ A}$	$V_F$		1,00		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$	$I_R$		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	$R_{thJC}$		1,20	1,35	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		1,15		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$				$^{\circ}\text{C}$

prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0

初步数据  
Preliminary Data

IGBT, 斩波器 / IGBT-Chopper  
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 75^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	40 50	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	80	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$P_{\text{tot}}$	180	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,05 2,50 2,60	2,40	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 1,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,0	5,8	6,5 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,185		$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	0,0		$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	2,35		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,13		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{don}$	0,035 0,035 0,035		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,02 0,025 0,025		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{doff}$	0,23 0,29 0,31		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,02 0,04 0,05		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1800\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	2,00 3,10 3,50		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4300\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 12\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	1,50 2,40 2,70		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		$I_{SC}$	130		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$	0,55	0,70	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,55		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0



初步数据  
Preliminary Data

Diode-斩波器 / Diode-Chopper  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
连续正向直流电流 Continuous DC forward current		$I_F$	25	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	30	A
I <sup>2</sup> t-值 I <sup>2</sup> t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	310	A <sup>2</sup> s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	2,00 1,70 1,65	2,55	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 25\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	30,0 45,0 50,0		A A A
恢复电荷 Recovered charge	$I_F = 25\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	1,50 3,50 4,00		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 25\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	0,70 1,75 2,15		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$	0,70	0,75	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,70		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^{\circ}\text{C}$	$R_{25}$		5,00		k $\Omega$
R100 偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{25}$			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0



初步数据  
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	2,5		kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		11,5 6,3		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		10,0 5,0		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
杂散电感,模块 Stray inductance module		L <sub>sCE</sub>		25	nH
储存温度 Storage temperature		T <sub>stg</sub>	-40		125 °C
Anpresskraft für mech. Bef. pro Feder mounting force per clamp		F	40	-	80 N
重量 Weight		G		36	g

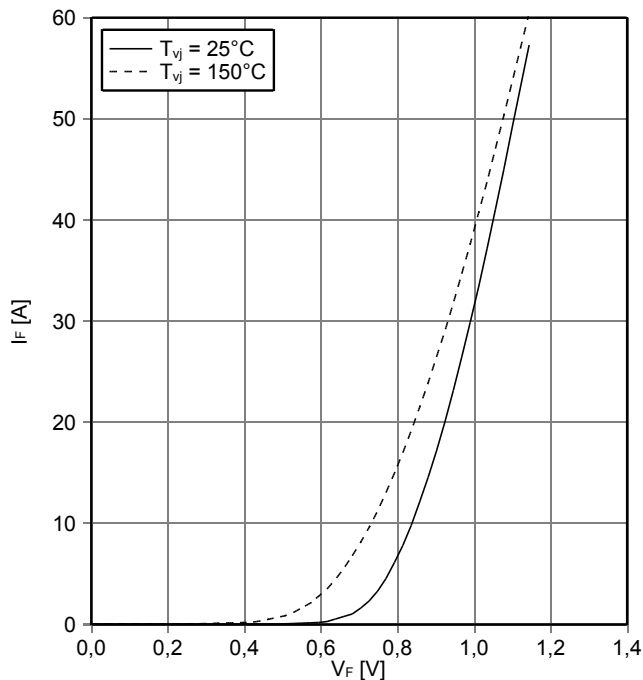
Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.  
The current under continuous operation is limited to 25A rms per connector pin.

prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0

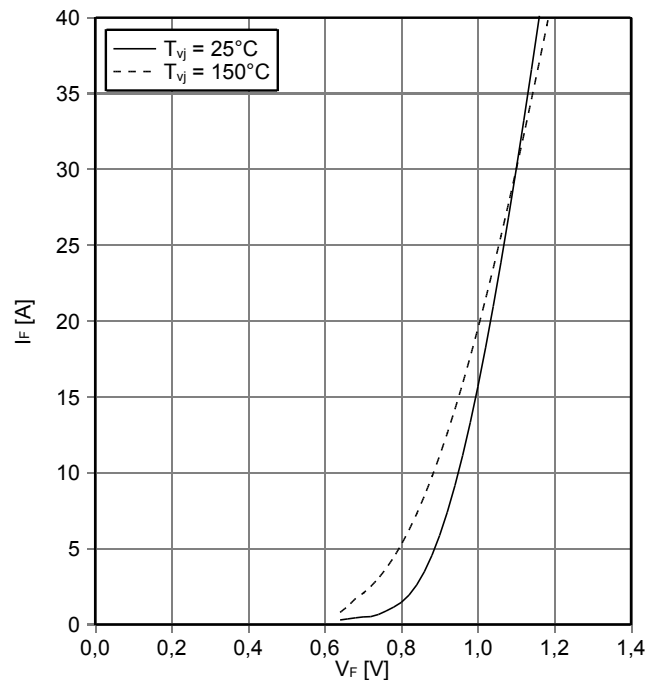


初步数据  
Preliminary Data

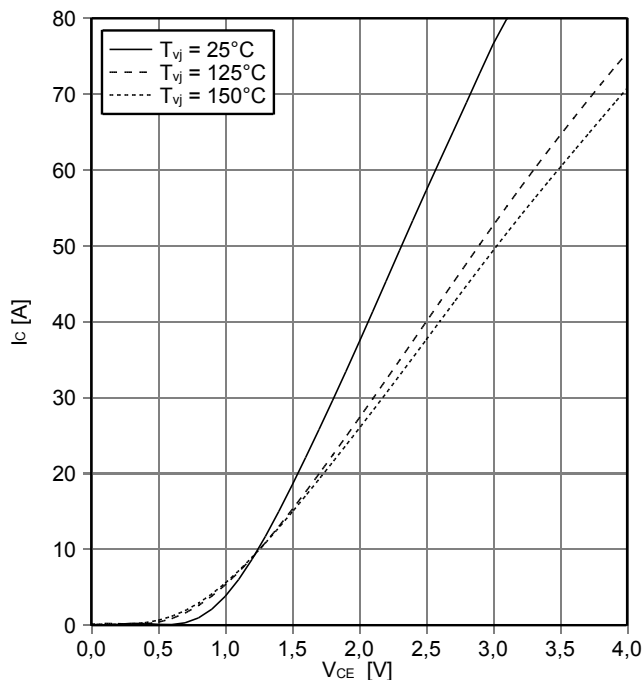
正向偏压特性 反极性保护二极管A (典型)  
forward characteristic of Inverse-polarity protection diode A (typical)  
 $I_F = f(V_F)$



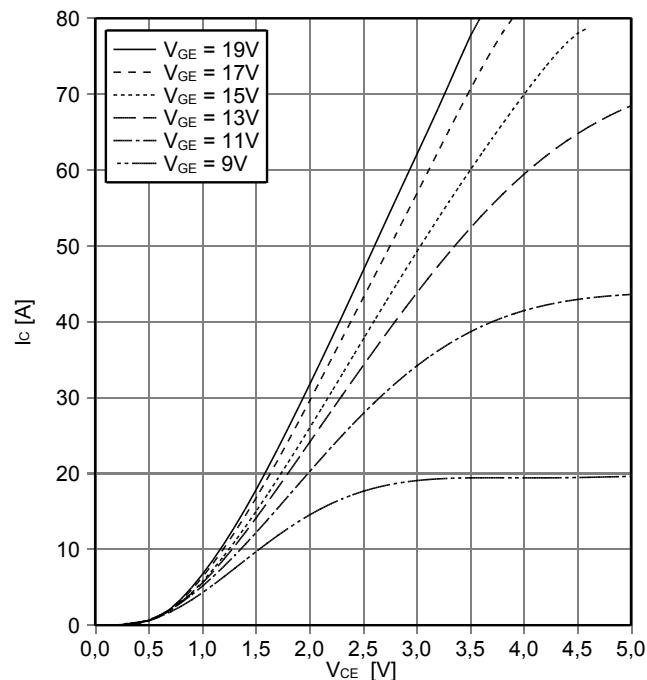
正向偏压特性 反极性保护二极管B (典型)  
forward characteristic of Inverse-polarity protection diode B (typical)  
 $I_F = f(V_F)$



输出特性 IGBT, 斩波器 (典型)  
output characteristic IGBT-Chopper (typical)  
 $I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 斩波器 (典型)  
output characteristic IGBT-Chopper (typical)  
 $I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



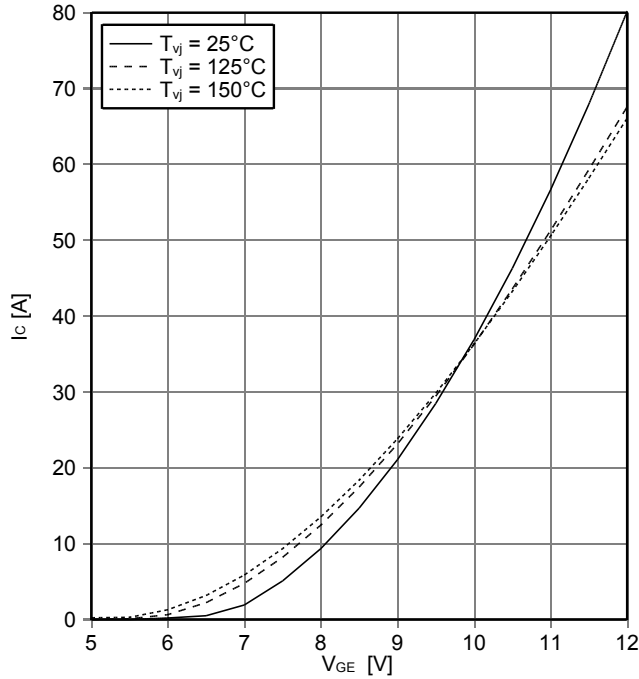
prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0



初步数据  
Preliminary Data

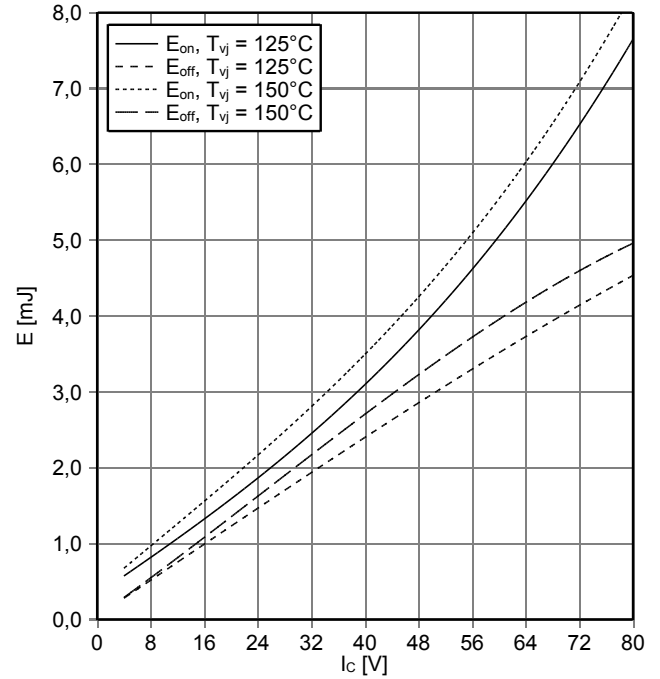
传输特性 IGBT, 斩波器 (典型)  
transfer characteristic IGBT-Chopper (typical)

$I_c = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



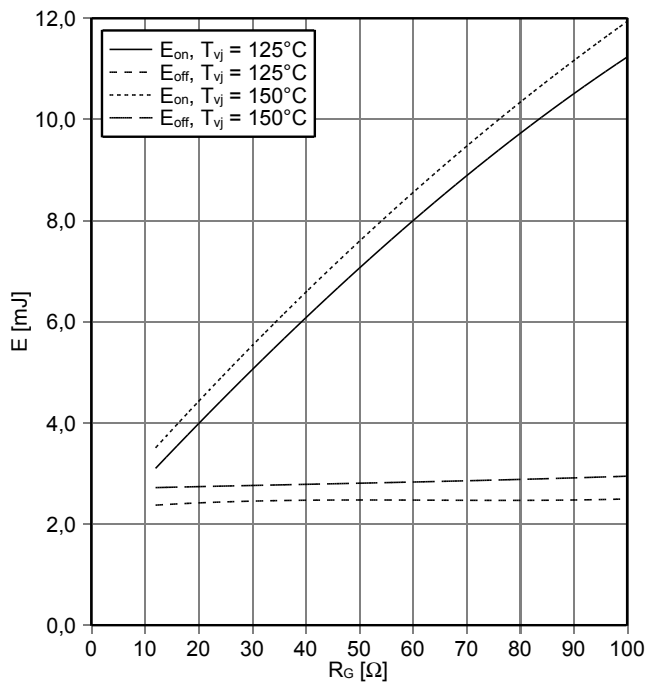
开关损耗 IGBT, 斩波器 (典型)  
switching losses IGBT-Chopper (typical)

$E_{on} = f(I_c)$ ,  $E_{off} = f(I_c)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 12\ \Omega$ ,  $R_{Goff} = 12\ \Omega$ ,  $V_{CE} = 600\text{ V}$



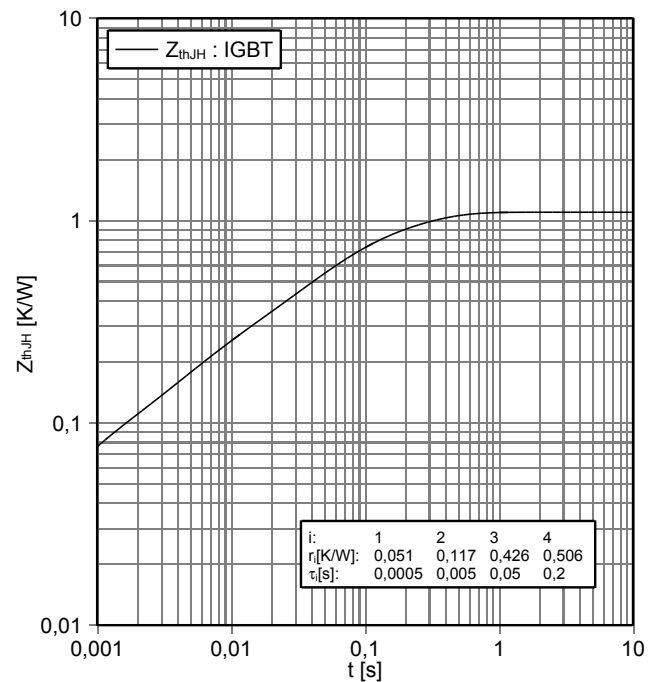
开关损耗 IGBT, 斩波器 (典型)  
switching losses IGBT-Chopper (typical)

$E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $I_c = 40\text{ A}$ ,  $V_{CE} = 600\text{ V}$



瞬态热阻抗 IGBT, 斩波器  
transient thermal impedance IGBT-Chopper

$Z_{thJH} = f(t)$



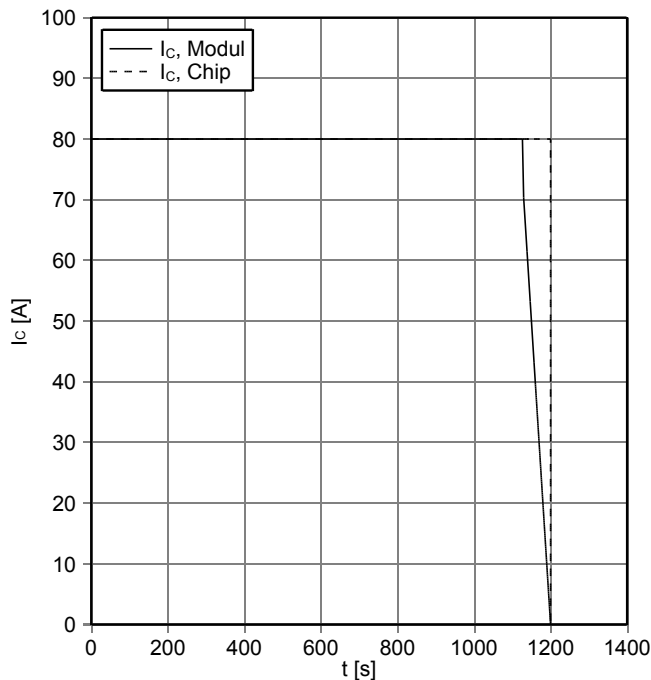
prepared by: CM	date of publication: 2013-11-25
approved by: MB	revision: 2.0



初步数据  
Preliminary Data

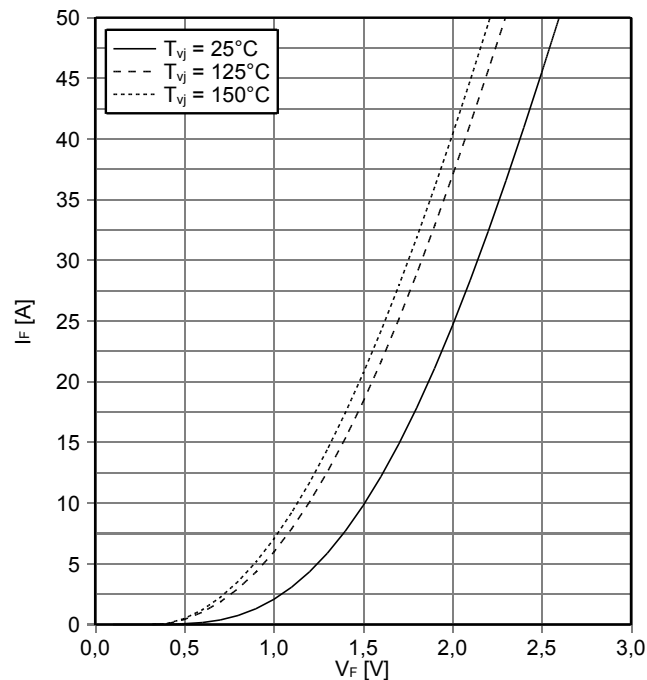
反偏安全工作区 IGBT, 斩波器 (RBSOA)  
reverse bias safe operating area IGBT-Chopper (RBSOA)

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Goff} = 12\ \Omega$ ,  $T_{vj} = 150^\circ\text{C}$



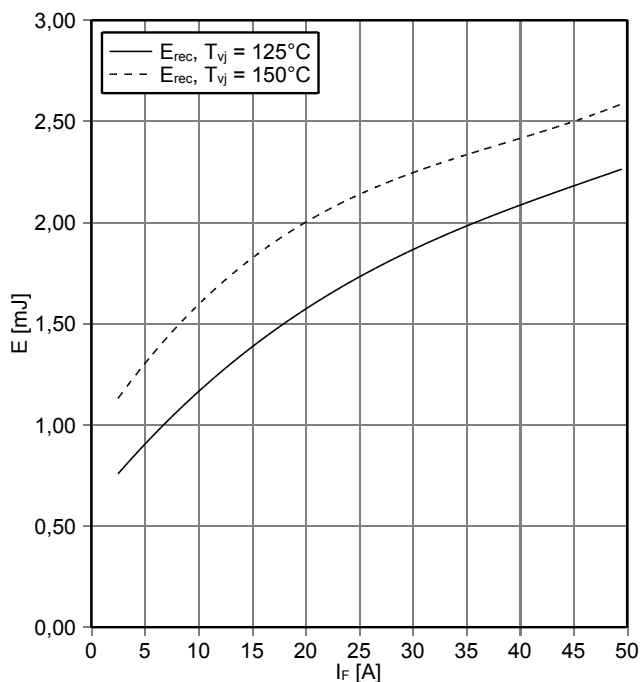
正向偏压特性 Diode-斩波器 (典型)  
forward characteristic of Diode-Chopper (typical)

$I_F = f(V_F)$



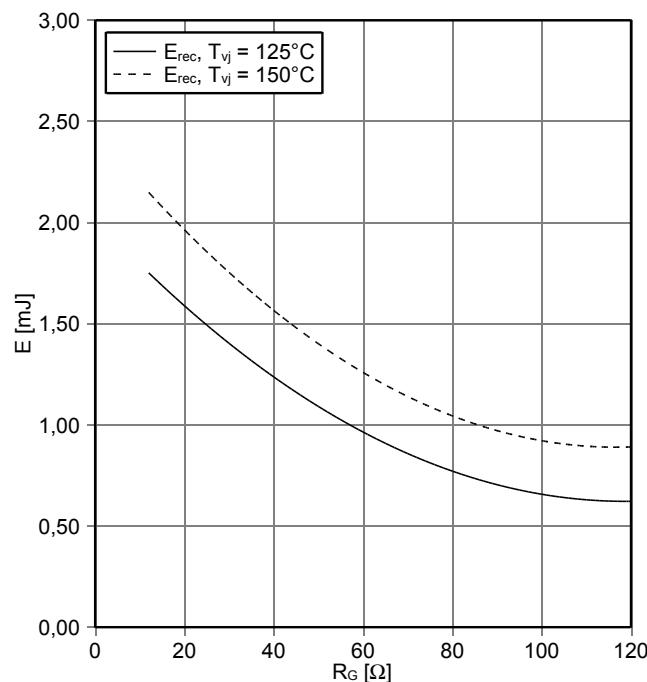
开关损耗 Diode-斩波器 (典型)  
switching losses Diode-Chopper (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 12\ \Omega$ ,  $V_{CE} = 600\text{ V}$



开关损耗 Diode-斩波器 (典型)  
switching losses Diode-Chopper (typical)

$E_{rec} = f(R_G)$   
 $I_F = 25\text{ A}$ ,  $V_{CE} = 600\text{ V}$



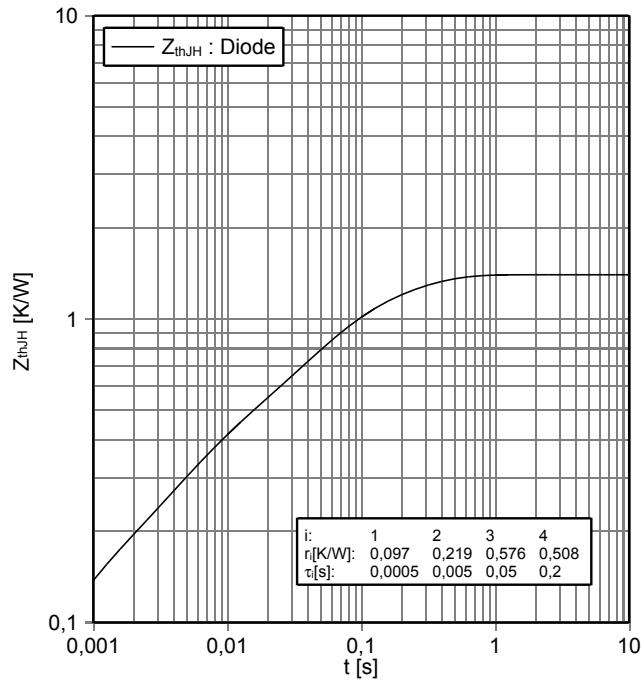
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approved by: MB	revision: 2.0



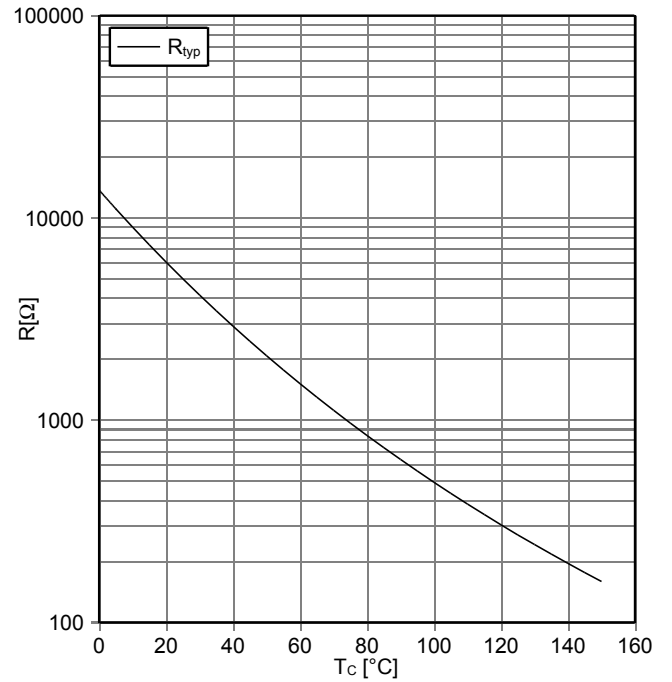


初步数据  
Preliminary Data

瞬态热阻抗 Diode-斩波器  
transient thermal impedance Diode-Chopper  
 $Z_{thJH} = f(t)$

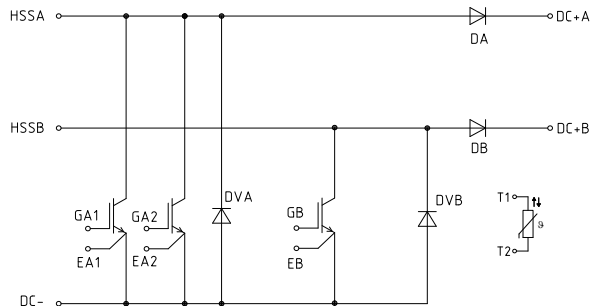


负温度系数热敏电阻 温度特性  
NTC-Thermistor-temperature characteristic (typical)  
 $R = f(T)$

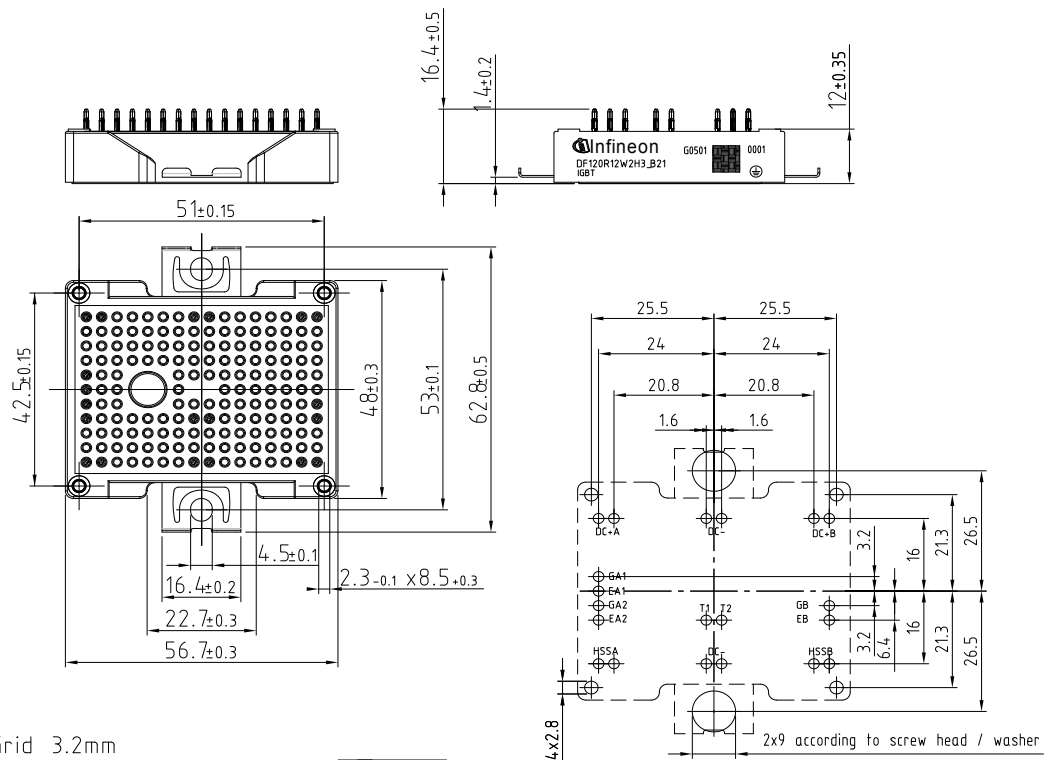


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接线图 / circuit\_diagram\_headline



封装尺寸 / package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern  $\varnothing 0.1$
- Hole specification for contacts see AN 2009-09
- Diameters of plated holes  $\varnothing 1.0\text{mm}$
- Diameters of drill  $\varnothing 1.15\text{mm}$

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**初步数据  
Preliminary Data**

**使用条件和条款**

**使用条件和条款**

产品规格书中的数据是专门为技术人员提供的，您和您的技术部门应该针对您的应用来评估产品及产品的所有参数是否适合

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请注意，对这类应用我们强烈建议

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-得到质量协议的结论

-建立联合的测试和出厂产品检查，我们可以根据测试的实际情况供货

如果有必要，请根据实际需要将类似的说明给你的客户

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**Terms & Conditions of usage**

The data contained in this product data sheet is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application.

This product data sheet is describing the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its characteristics. The information in the valid application- and assembly notes of the module must be considered.

Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you ( see [www.infineon.com](http://www.infineon.com) ). For those that are specifically interested we may provide application notes.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the Product in aviation applications, in health or live endangering or life support applications, please notify. Please note, that for any such applications we urgently recommend

- to perform joint Risk and Quality Assessments;

- the conclusion of Quality Agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

If and to the extent necessary, please forward equivalent notices to your customers.

Changes of this product data sheet are reserved.

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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